

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	233	(semiconductor or wafer or substrate) and source and drain and p-type and n-type and (drain near4 drift) and (drain near4 contact) and dop\$4 and ((insulat\$4 or oxide or dielectric) near4 gate) and channel and strip\$4 and voltage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 10:16
S2	8	(semiconductor or wafer or substrate) and source and drain and p-type and n-type and (drain near4 drift) and (drain near4 contact) and dop\$4 and ((insulat\$4 or oxide or dielectric) near4 gate) and channel and strip\$4 and voltage and localis\$4 and (trench or via of hole) and deplet\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/27 14:17
S3	22505	(localize\$4 near4 region)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 10:16
S4	1	(localize\$4 near4 region) near9 (drain near drift)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 10:17
S5	286	(localize\$4 near4 region) near9 drain	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 10:17
S6	67	(localize\$4 near4 region) near9 drain near9 channel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 10:17
S7	1	(localize\$4 near4 region) near9 drain near9 channel and (alternat\$4 near9 conductivity)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 10:18

EAST Search History

S8	1	(localize\$4 near4 region) near9 drain near9 channel and (alternat\$4 near9 (conductivity or nnp or pnp))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/05 10:18
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